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HUF75345G3, HUF75345P3, HUF75345S3S

Data Sheet

October 2013

N-Channel UltraFET Power MOSFET 55 V, 75 A, 7 m Ω

These N-Channel power MOSFETs are manufactured using the innovative UltraFET process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

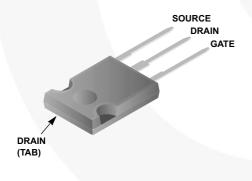
Formerly developmental type TA75345.

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75345G3	TO-247	75345G
HUF75345P3	TO-220AB	75345P
HUF75345S3ST	TO-263AB	75345S

Packaging

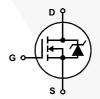
JEDEC STYLE TO-247



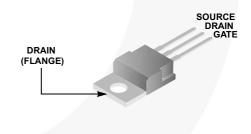
Features

- 75A, 55V
- · Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Models
 - Thermal Impedance SPICE and SABER Models Available on the WEB at: www.fairchildsemi.com
- · Peak Current vs Pulse Width Curve
- UIS Rating Curve
- · Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



JEDEC TO-220AB



JEDEC TO-263AB



Product reliability information can be found at http://www.fairchildsemi.com/products/discrete/reliability/index.html
For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF75345G3, HUF75345P3, HUF75345S3S

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

		UNITS
Drain to Source Voltage (Note 1)V _{DSS}	55	V
Drain to Gate Voltage (R _{GS} = 20kΩ) (Note 1)	55	V
Gate to Source Voltage	±20	V
Drain Current		
Continuous (Figure 2)	75	Α
Pulsed Drain Current	Figure 4	
Pulsed Avalanche RatingE _{AS}	Figure 6	
Power Dissipation	325	W
Derate Above 25 ^o C	2.17	W/oC
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	οС
Package Body for 10s, See Techbrief 334	260	°С

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN	TYP	MAX	UNITS
OFF STATE SPECIFICATIONS	'						
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} =	0V (Figure 11)	55	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 50V, V _{GS} =	0V	-	-	1	μΑ
		V _{DS} = 45V, V _{GS} =	0V, T _C = 150 ^o C	-	-	250	μА
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
ON STATE SPECIFICATIONS	•					•	
Gate to Source Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = 2$	50μA (Figure 10)	2	-	4	V
Drain to Source On Resistance	r _{DS(ON)}	I _D = 75A, V _{GS} = 10	V (Figure 9)	-	0.006	0.007	Ω
THERMAL SPECIFICATIONS			/-		1		
Thermal Resistance Junction to Case	$R_{ heta JC}$	(Figure 3)		-	-	0.46	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247		/ -	-	30	°C/W
		TO-220, TO-263		-	-	62	°C/W
SWITCHING SPECIFICATIONS (V _{GS} = 10)	V)		- /	1	1		
Turn-On Time	ton	$V_{DD} = 30V, I_{D} \cong 75A,$ $R_{L} = 0.4\Omega, V_{GS} = 10V,$ $R_{GS} = 2.5\Omega$		-	-	195	ns
Turn-On Delay Time	t _{d(ON)}			-	14	/- <u>-</u>	ns
Rise Time	t _r			-	118	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	42	-	ns
Fall Time	t _f			-	26	-	ns
Turn-Off Time	tOFF			-	- /	98	ns
GATE CHARGE SPECIFICATIONS	'						
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	V _{DD} = 30V,	-	220	275	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V	$ I_D \cong 75A, $ $ R_L = 0.4\Omega $ $ I_{g(REF)} = 1.0 \text{mA} $	-	125	165	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V		-	6.8	10	nC
Gate to Source Gate Charge	Q _{gs}		(Figure 13)	-	14	-	nC
Gate to Drain "Miller" Charge	Q _{gd}			-	58	-	nC

HUF75345G3, HUF75345P3, HUF75345S3S

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V,	-	4000	-	pF
Output Capacitance	Coss	f = 1MHz (Figure 12)	-	1450	-	pF
Reverse Transfer Capacitance	C _{RSS}	(rigure 12)	-	450	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V _{SD}	I _{SD} = 75A	-	-	1.25	V
Reverse Recovery Time	t _{rr}	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	55	ns
Reverse Recovered Charge	Q _{RR}	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	80	nC

Typical Performance Curves

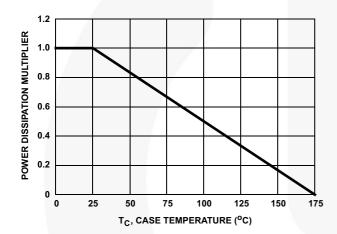


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

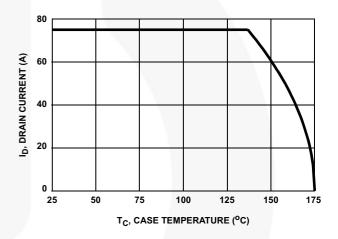


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

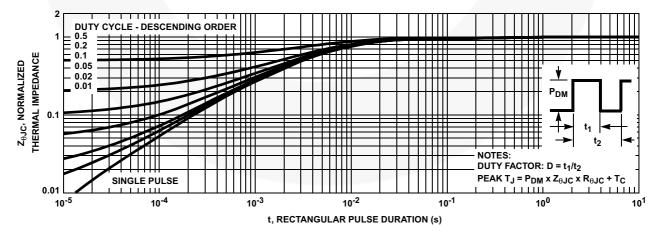


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves (Continued)

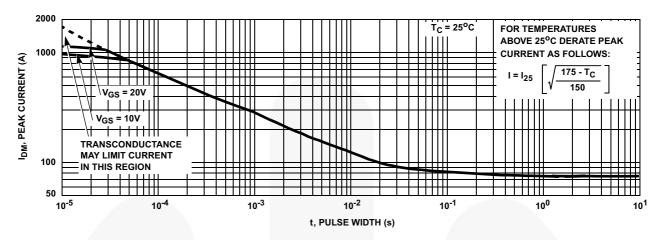


FIGURE 4. PEAK CURRENT CAPABILITY

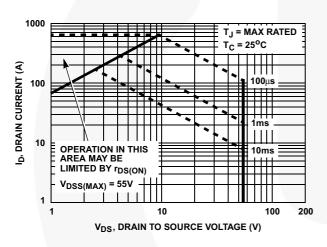


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA

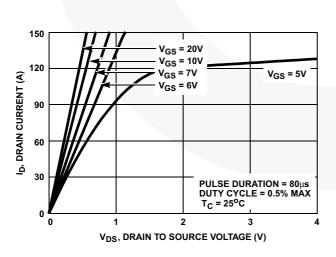
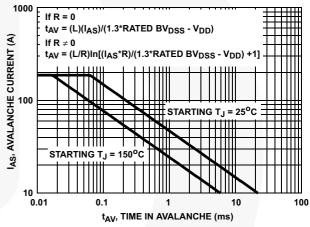


FIGURE 7. SATURATION CHARACTERISTICS



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322. FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

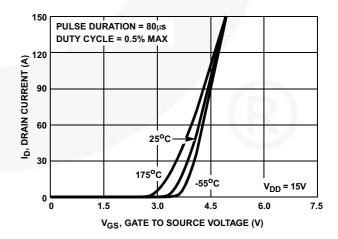


FIGURE 8. TRANSFER CHARACTERISTICS

1.2

Typical Performance Curves (Continued)

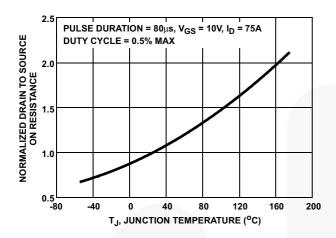


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

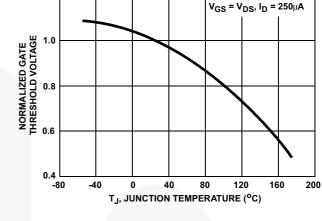


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

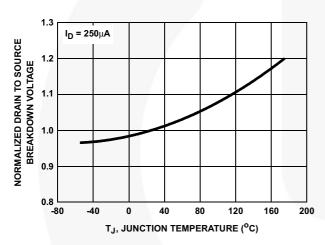


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

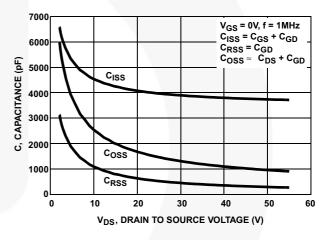
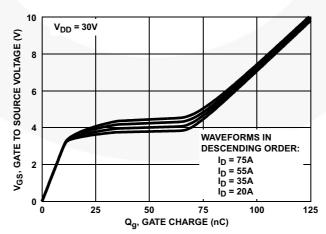


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

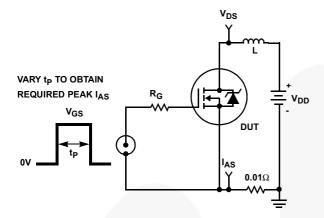


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

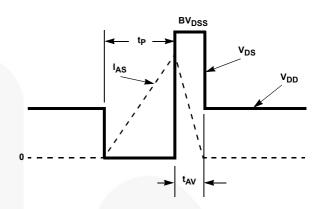


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

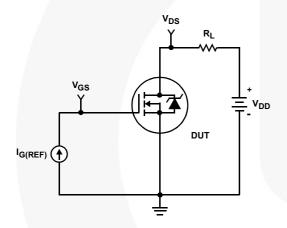


FIGURE 16. GATE CHARGE TEST CIRCUIT

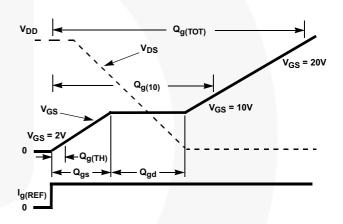


FIGURE 17. GATE CHARGE WAVEFORM

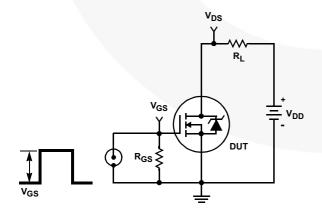


FIGURE 18. SWITCHING TIME TEST CIRCUIT

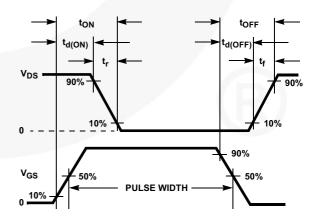


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

PSPICE Electrical Model

```
.SUBCKT HUF75345 2 1 3 :
                                  rev 3 Feb 99
CA 12 8 5.55e-9
CB 15 14 5.55e-9
                                                                                                                    LDRAIN
CIN 6 8 3.45e-9
                                                                        DPLCAP
                                                                                                                              DRAIN
                                                                    10
DBODY 7 5 DBODYMOD
                                                                                                                   RLDRAIN
DBREAK 5 11 DBREAKMOD
                                                                                   ≯RSLC1
                                                                                                  DBREAK
DPLCAP 10 5 DPLCAPMOD
                                                                                    51
                                                                      RSLC2
                                                                                       ESLC
                                                                                                          11
FBRFAK 11 7 17 18 56 7
EDS 14 8 5 8 1 EGS 13 8 6 8 1
                                                                                     50
                                                                                                           17
18
                                                                                                                ▲ DBODY
                                                                                   ≶rdrain
ESG 6 10 6 8 1
                                                                                                 EBREAK
                                                             ESG
EVTHRES 6 21 19 8 1
                                                                         EVTHRES
EVTEMP 20 6 18 22 1
                                                                           (19)
8
                                                                                                   MWEAK
                                           LGATE
                                                           EVTEMP
                                  GATE
                                                    RGATE
IT 8 17 1
                                                                                          MMED
                                                   q
                                                          20
                                                                                   MSTRO
                                          RLGATE
LDRAIN 2 5 1e-9
LGATE 1 9 2.6e-9
                                                                                                                   LSOURCE
                                                                              CIN
                                                                                                                              SOURCE
LSOURCE 3 7 1.1e-9
                                                                                        8
KGATE LSOURCE LGATE 0.0085
                                                                                                   RSOURCE
                                                                                                                   RLSOURCE
MMED 16 6 8 8 MMEDMOD
MSTRO 16 6 8 8 MSTROMOD
                                                            S1A
                                                                       S2A
                                                                                                       RBREAK
MWEAK 16 21 8 8 MWEAKMOD
                                                                              15
                                                                13
8
                                                                     <u>14</u>
13
                                                                                                   17
                                                                                                                 18
RBREAK 17 18 RBREAKMOD 1
                                                                                                                 RVTEMP
                                                            S<sub>1</sub>B
                                                                       S2B
RDRAIN 50 16 RDRAINMOD 1e-4
                                                                   13
RGATE 9 20 0.36
                                                                              CB
                                                                                                                 19
                                                      CA
RLDRAIN 2 5 10
                                                                                                 IT
                                                                                    14
RLGATE 1926
                                                                                                                   VBAT
RLSOURCE 3 7 11
                                                               EGS
                                                                           EDS
RSLC1 5 51 RSLCMOD 1e-6
                                                                                               8
RSLC2 5 50 1e3
RSOURCE 8 7 RSOURCEMOD 3.15e-3
                                                                                                       RVTHRES
RVTHRES 22 8 RVTHRESMOD 1
RVTEMP 18 19 RVTEMPMOD 1
S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD
VBAT 22 19 DC 1
ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*500),3.5))}
.MODEL DBODYMOD D (IS = 6e-12 RS = 1.4e-3 IKF = 20 XTI = 5 TRS1 = 2.75e-3 TRS2 = 5.0e-6 CJO = 5.5e-9 TT = 5.9e-8 M = 0.5 VJ = 0.75)
.MODEL DBREAKMOD D (RS = 2.8e-2 IKF = 30 TRS1 = -4.0e-3 TRS2 = 1.0e-6)
.MODEL DPLCAPMOD D (CJO = 6.75e-9 IS = 1e-30 M = 0.88 VJ = 1.45 FC = 0.5)
.MODEL MMEDMOD NMOS (VTO = 2.93 KP = 13.75 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 0.36)
.MODEL MSTROMOD NMOS (VTO = 3.23 KP = 96 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u Lambda = 0.06)
.MODEL MWEAKMOD NMOS (VTO = 2.35 KP =0.02 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 3.6)
.MODEL RBREAKMOD RES (TC1 = 8.0e-4 TC2 = 4.0e-6)
.MODEL RDRAINMOD RES (TC1 = 1.5e-1 TC2 = 6.5e-4)
.MODEL RSLCMOD RES (TC1 = 1.0e-4 TC2 = 1.05e-6)
.MODEL RSOURCEMOD RES (TC1 = 1.0e-3 TC2 = 0)
.MODEL RVTHRESMOD RES (TC1 = -1.5e-3 TC2 = -2.6e-5)
.MODEL RVTEMPMOD RES (TC1 = -2.75e-3 TC2 = 1.45e-6)
.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -9.00 VOFF= -4.00)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -4.00 VOFF= -9.00)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.00 VOFF= 0.50)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.50 VOFF= 0.00)
.ENDS
```

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

SABER Electrical Model

```
REV 3 February 1999
template huf75345 n2, n1, n3
electrical n2. n1. n3
var i iscl
d..model dbodymod = (is = 6e-12, xti = 5, cjo = 5.5e-9, tt = 5.9e-8, m=0.5, vj=0.75)
d..model dbreakmod = ()
d..model dplcapmod = (cjo = 6.75e-9, is = 1e-30, m = 0.88, vj = 1.45, fc=0.5)
m..model mmedmod = (type= n, vto = 2.93, kp = 13.75, is = 1e-30, tox = 1)
m..model mstrongmod = (type=_n, vto = 3.23, kp = 96, is=1e-30,tox=1,
                                                                                                                                    LDRAIN
                                                                                    DPLCAP
                                                                                                                                               DRAIN
m..model mweakmod = (type=_n, vto = 2.35, kp = 0.02, is = 1e-30, tox = 1)
sw_vcsp..model s1amod = (ron = 1e-5, roff = 0.1, von = -9, voff = -4)
                                                                                10
sw_vcsp..model s1bmod = (ron = 1e-5, roff = 0.1, von = -4, voff = -9)
                                                                                                                                   RLDRAIN
                                                                                                 RSLC1
sw_vcsp..model s2amod = (ron = 1e-5, roff = 0.1, von = 0, voff = 0.5)
                                                                                                              RDBREAK
                                                                                                 51
sw_vcsp..model s2bmod = (ron = 1e-5, roff = 0.1, von = 0.5, voff = 0)
                                                                                  RSLC2 €
                                                                                                                       72
                                                                                                                                   RDBODY
                                                                                                    ISCL
c.ca n12 n8 = 5.55e-9
c.cb n15 n14 = 5.55e-9
                                                                                                               DBREAK
c.cin n6 n8 = 3.45e-9
                                                                                                  50
                                                                                                 RDRAIN
                                                                        ESG
                                                                                                                        11
d.dbody n7 n71 = model=dbodymod
                                                                                     EVTHRES
d.dbreak n72 n11 = model=dbreakmod
                                                                                                     16
                                                                                                 21
d.dplcap n10 n5 = model=dplcapmod
                                                                                        1<u>9</u>
8
                                                                                                                  MWEAK
                                                                       EVTEMP
                                                                                                                                   DBODY
                                                              RGATE
i.it n8 n17 = 1
                                                                                                                  EBREAK
                                                                         18
22
                                                                                                        MMED
                                                                     20
                                                                                                 MSTRO
I.ldrain n2 n5 = 1e-9
                                                    RLGATE
I.lgate n1 n9 = 2.6e-9
                                                                                                                                   LSOURCE
                                                                                           CIN
                                                                                                                                              SOURCE
I.Isource n3 n7 = 1.1e-9
                                                                                                     8
k.k1 i(l.lgate) i(l.lsource) = l(l.lgate), l(l.lsource), 0.0085
                                                                                                                 RSOURCE
                                                                                                                                  RLSOURCE
m.mmed n16 n6 n8 n8 = model=mmedmod, I = 1u, w = 1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, I = 1u, w = 1u
                                                                                                                     RBREAK
m.mweak n16 n21 n8 n8 = model=mweakmod, I = 1u, w = 1u
                                                                                          15
res.rbreak n17 n18 = 1, tc1 = 8e-4, tc2 = 4e-6
                                                                                                                               ≶ RVTEMP
                                                                       S1B
                                                                                   S2B
res.rdbody n71 n5 = 1.4e-3, tc1 = 2.75e-3, tc2 = 5e-6
res.rdbreak n72 n5 = 2.8e-2, tc1 = -4e-3, tc2 = 1e-6
                                                                                           СВ
                                                                                                                                 19
                                                                 CA
                                                                                                                IT
res.rdrain n50 n16 = 1e-4, tc1 = 1.5e-1, tc2 = 6.5e-4
                                                                                                                                   VBAT
res.rgate n9 n20 = 0.36
                                                                          EGS
                                                                                        EDS
res.rldrain n2 n5 = 10
res.rlgate n1 n9 = 26
                                                                                                             8
res.rlsource n3 n7 = 11
                                                                                                                     RVTHRES
res.rslc1 n5 n51 = 1e-6, tc1 = 1e-4, tc2 = 1.05e-6
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 3.15e-3, tc1 = 1e-3, tc2 = 0
res.rvtemp n18 n19 = 1, tc1 = -2.75e-3, tc2 = 1.45e-6
res.rvthres n22 n8 = 1, tc1 = -1.5e-3, tc2 = -2.6e-5
spe.ebreak n11 n7 n17 n18 = 56.7
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1
sw vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
v.vbat n22 n19 = dc = 1
equations {
i(n51->n50) + = iscl
|sc| = v(n51, n50) = ((v(n5, n51)/(1e-9+abs(v(n5, n51))))*((abs(v(n5, n51)*1e6/500))** 3.5))
```

SPICE Thermal Model

REV 5 February 1999

HUF75345

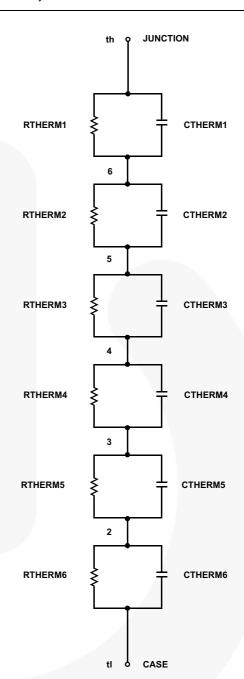
CTHERM1 th 6 6.3e-3
CTHERM2 6 5 1.5e-2
CTHERM3 5 4 2.0e-2
CTHERM4 4 3 3.0e-2
CTHERM5 3 2 8.0e-2
CTHERM6 2 tl 1.5e-1

RTHERM1 th 6 5.0e-3
RTHERM2 6 5 1.8e-2
RTHERM3 5 4 5.0e-2
RTHERM4 4 3 8.5e-2
RTHERM5 3 2 1.0e-1
RTHERM6 2 tl 1.1e-1

SABER Thermal Model

SABER thermal model HUF75345

template thermal_model th tl thermal_c th, tl $\{$ ctherm.ctherm1 th 6=6.3e-3 ctherm.ctherm2 6.5=1.5e-2 ctherm.ctherm3 5.4=2.0e-2 ctherm.ctherm4 4.3=3.0e-2 ctherm.ctherm5 3.2=8.0e-2 ctherm.ctherm6 2.tl=1.5e-1 rtherm.rtherm1 th 6=5.0e-3 rtherm.rtherm2 6.5=1.8e-2 rtherm.rtherm3 5.4=5.0e-2 rtherm.rtherm4 4.3=8.5e-2 rtherm.rtherm5 3.2=1.0e-1 rtherm.rtherm6 2.tl=1.1e-1



Mechanical Dimensions

TO-220 3L

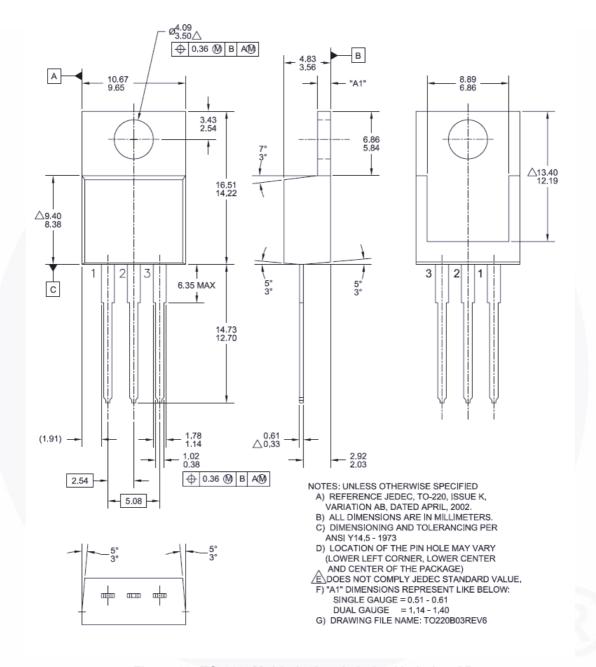


Figure 20. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters



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